Amendments to the Claims

1. (Original) A silicon epitaxial wafer having an excellent gettering capability in the entire radial direction thereof, wherein density of oxide precipitates detectable in the interior of a silicon single crystal substrate after epitaxial growth is $1\times10^9/cm^3$ or higher at any position in the radial direction.

2. (Original) The silicon epitaxial wafer according to claim 1, wherein the silicon single crystal substrate prior to the epitaxial growth has Grown-in precipitation nuclei formed in a growth step for silicon single crystal, and when the silicon single crystal substrate is heat treated in an oxidizing atmosphere, stacking faults in the form of a ring are not generated.

3. (Currently amended) The silicon epitaxial wafer according to claim 1 ~~or 2~~, wherein the silicon single crystal substrate prior to the epitaxial growth is a boron-doped substrate having resistivity of 0.1 Ω·cm or lower.

4. (Original) A process for manufacturing a silicon epitaxial wafer having an excellent gettering capability in the entire substrate comprising the steps of:

heat treating a substrate for growing Grown-in precipitation nuclei; and thereafter,

performing epitaxial growth on the substrate,

wherein there is used as the substrate a silicon single crystal wafer which has Grown-in precipitation nuclei formed in a growth step for silicon single crystal, and in which stacking faults in the form of a ring are not generated in a heat treatment in an oxidizing atmosphere.

5. (Original) The process for manufacturing a silicon epitaxial wafer according to claim 4, wherein the substrate is a boron-doped substrate having resistivity of 0.1 Ω·cm or lower.

6. (New) The silicon epitaxial wafer according to claim 2, wherein the silicon single crystal substrate prior to the epitaxial growth is a boron-doped substrate having resistivity of 0.1 Ω·cm or lower.